



650V Super-junction Power MOSFET

Description

650V Super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs, designed according to the SJ principle. The deep trench SJ MOSFET provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

Features

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger

TO-220F



TO-263



TO-220

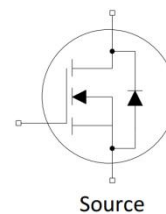


TO-247



Drain

Gate



Source



Device Marking and Package Information

Device	Package	Marking
TPA65R070D	TO-220F	65R070D
TPB65R070D	TO-263	65R070D
TPP65R070D	TO-220	65R070D
TPW65R070D	TO-247	65R070D

Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	0.07	Ω
$Q_{g,typ}$	80	nC
I_D	45	A
$I_{D,pulse}$	135	A
$E_{OSS} @ 400V$	10.3	μJ



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted				
Parameter		Symbol	Value	Unit
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	45	A
	$T_C = 100^\circ\text{C}$		27	
Pulsed Drain Current	(note1)	$I_{D,pulse}$	135	A
Gate-Source Voltage		V_{GSS}	± 30	V
Single Pulse Avalanche Energy	(note2)	E_{AS}	180	mJ
Avalanche Current		I_{AR}	6	A
Power Dissipation For TO-220F		P_D	53	W
Power Dissipation For TO-263, TO-220, TO-247			312	
Continuous Diode Forward Current		I_S	45	A
Diode Pulsed Current	(note1)	$I_{S,pulse}$	135	
Reverse Diode dv/dt	(note3)	dv/dt	50	V/ns
Maximum Diode Commutation Speed	(note3)	dv/dt	5	A/ μs
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance For TO-220F			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	2.35	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Thermal Resistance For TO-263, TO-220, TO-247			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	0.4	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	



Electrical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 650V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4.5	V
Drain-Source On-State-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 22A$	--	0.055	0.07	Ω
Dynamic Characteristics						
Input Capacitance	C_{ISS}	$V_{GS} = 0V,$ $V_{DS} = 100V,$ $f = 1.0\text{MHz}$	--	4134	--	pF
Output Capacitance	C_{OSS}		--	160	--	
Reverse Transfer Capacitance	C_{RSS}		--	4	--	
Total Gate Charge	Q_g	$V_{DD} = 400V, I_D = 22A,$ $V_{GS} = 10V$	--	80	--	nC
Gate-Source Charge	Q_{gs}		--	24	--	
Gate-Drain Charge	Q_{gd}		--	24	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 400V, I_D = 22A,$ $R_G = 25\Omega$	--	51	--	ns
Turn-on Rise Time	t_r		--	71	--	
Turn-off Delay Time	$t_{d(off)}$		--	154	--	
Turn-off Fall Time	t_f		--	67	--	
Drain-Source Body Diode Characteristics						
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 22A, V_{GS} = 0V$	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$V_R = 400V, I_S = 22A,$ $di_F/dt = 100A/\mu s$	--	354	--	ns
Reverse Recovery Charge	Q_{rr}		--	4.2	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	24	--	A

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. $V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1\%$



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

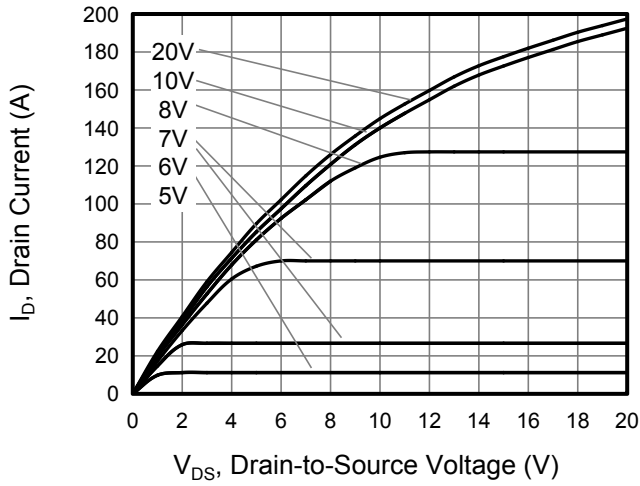


Figure 2. Transfer Characteristics

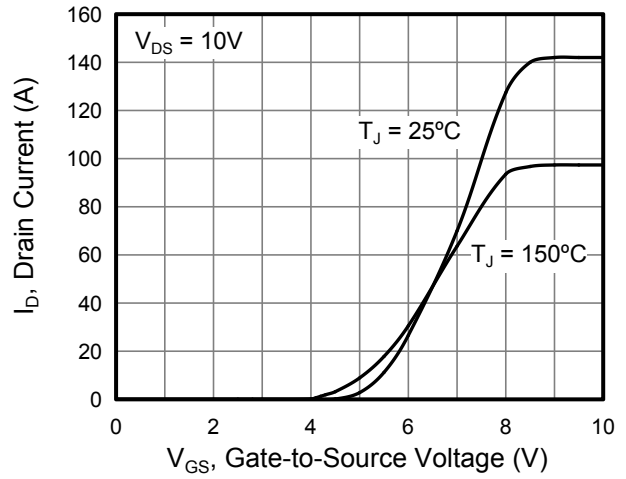


Figure 3. On-Resistance vs. Drain Current

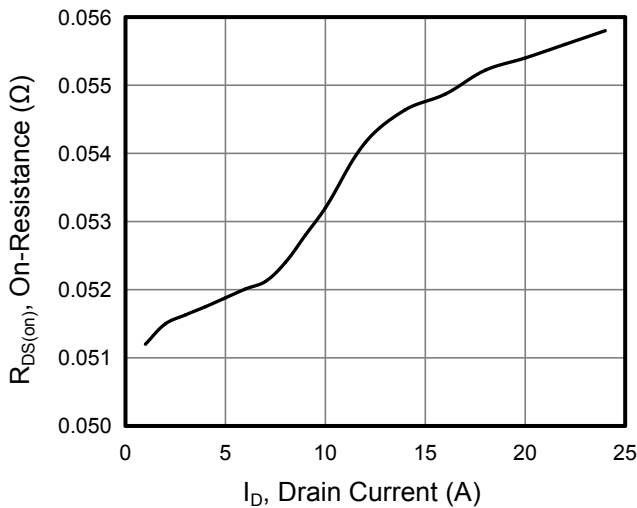


Figure 4. Capacitance

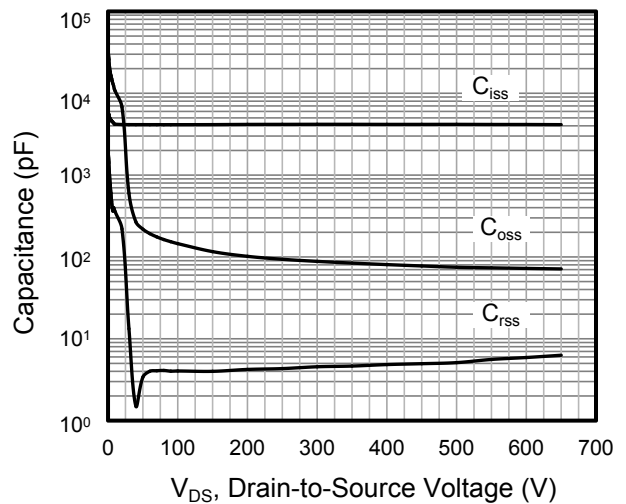


Figure 5. Gate Charge

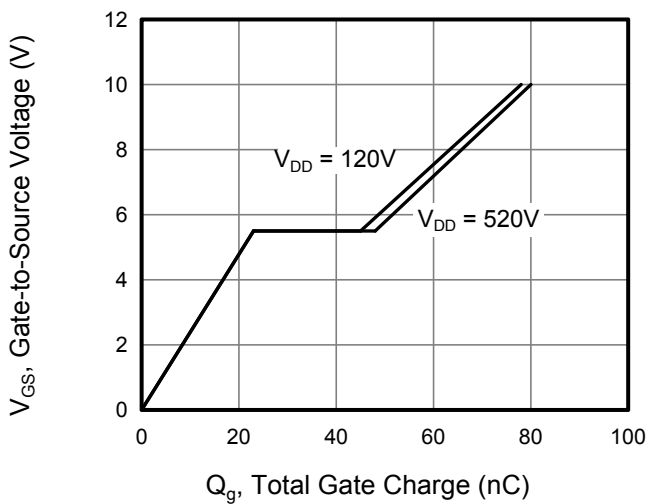


Figure 6. Body Diode Forward Voltage

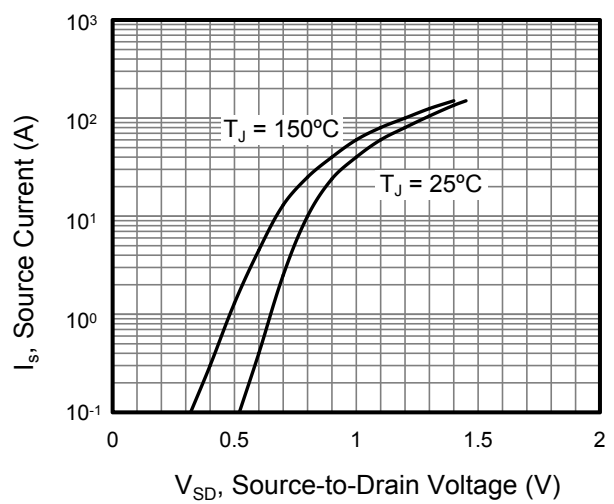




Figure 7. On-Resistance vs. Junction Temperature

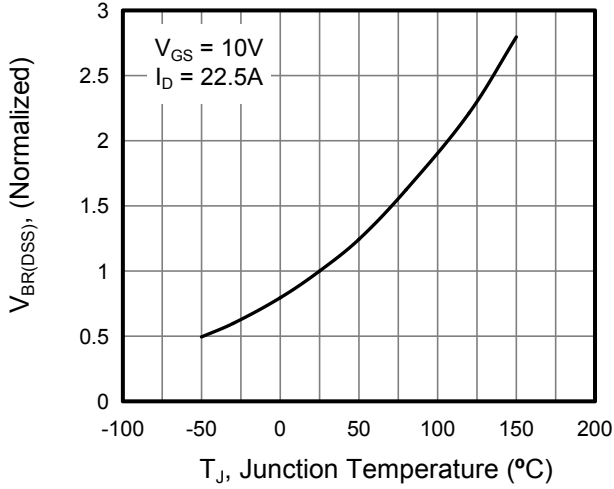


Figure 8. Breakdown voltage vs. Junction Temperature

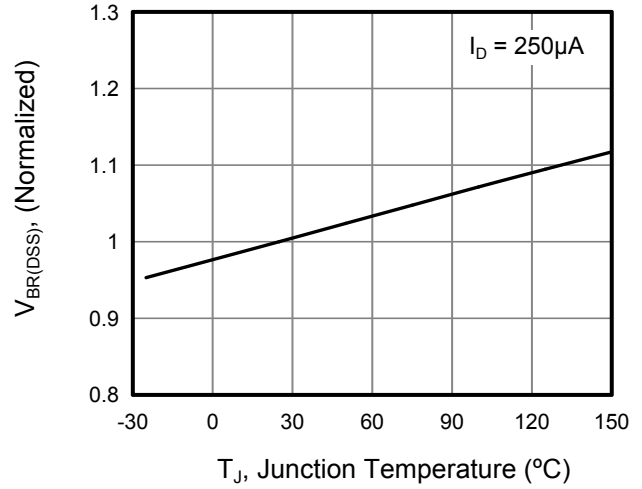


Figure 9. Transient Thermal Impedance For TO-220F

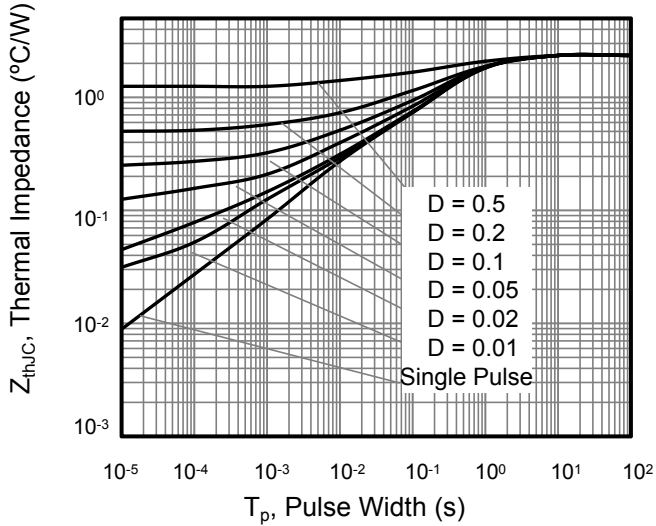


Figure 10. Transient Thermal Impedance For TO-263/TO-220/TO-247

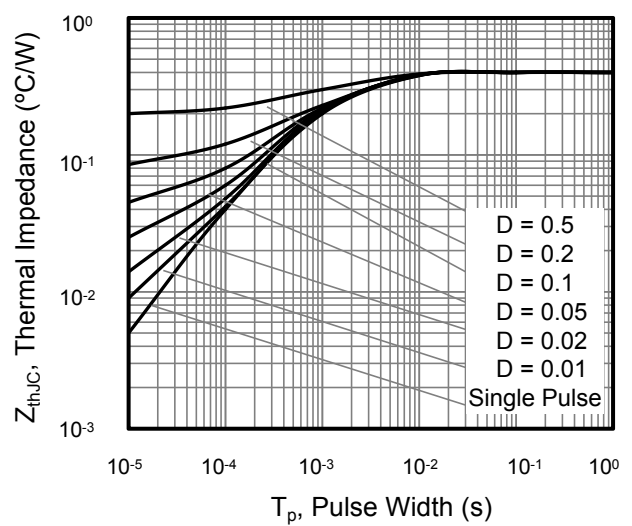


Figure 11. Safe Operation Area For TO-220F

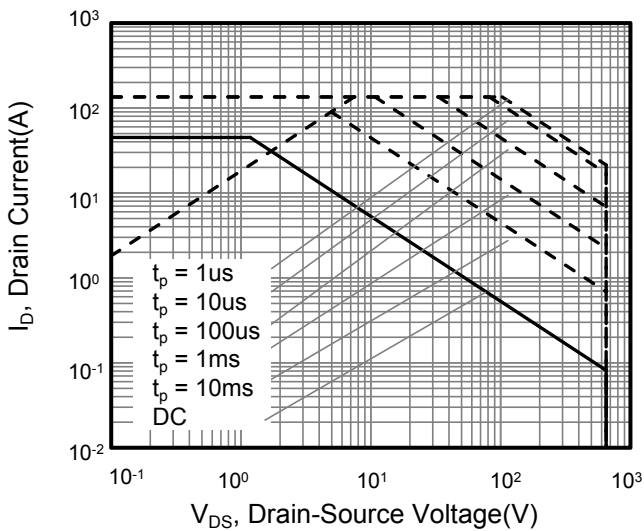
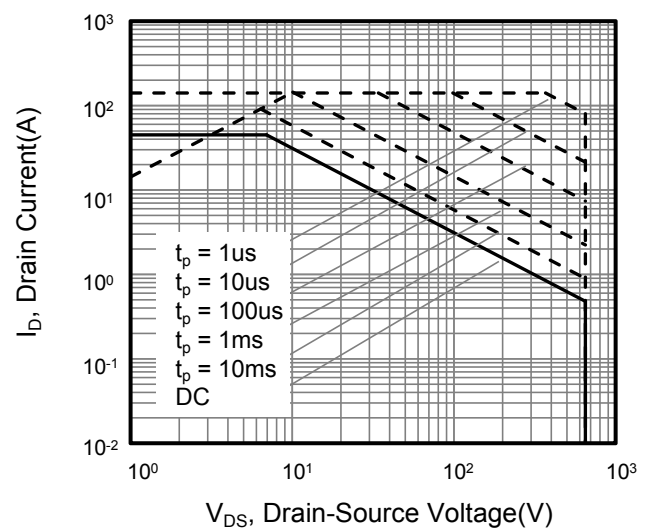


Figure 12. Safe Operation Area For TO-263/TO-220/TO-247





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 13. Typ. Coss Stored Energy

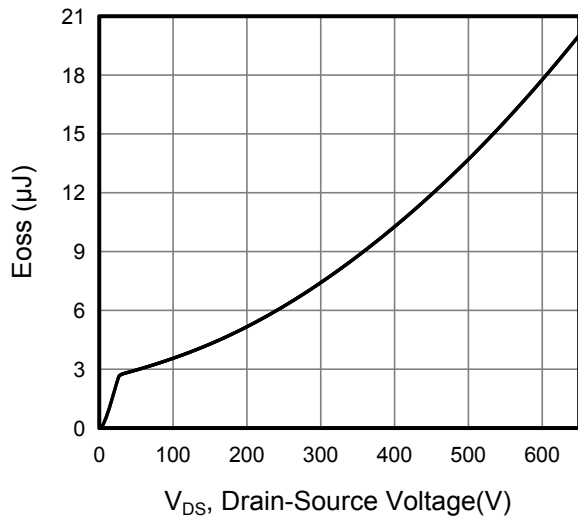




Figure A: Gate Charge Test Circuit and Waveform

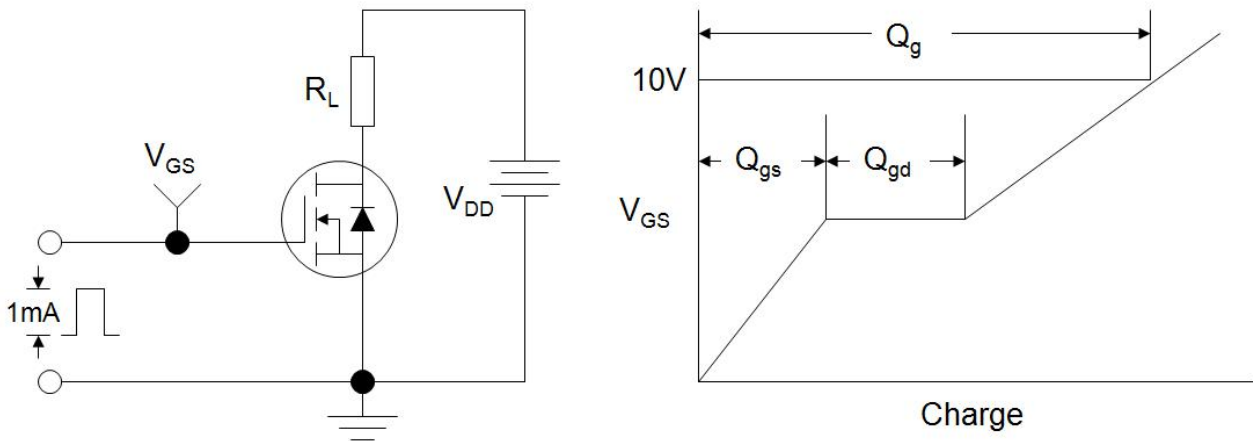


Figure B: Resistive Switching Test Circuit and Waveform

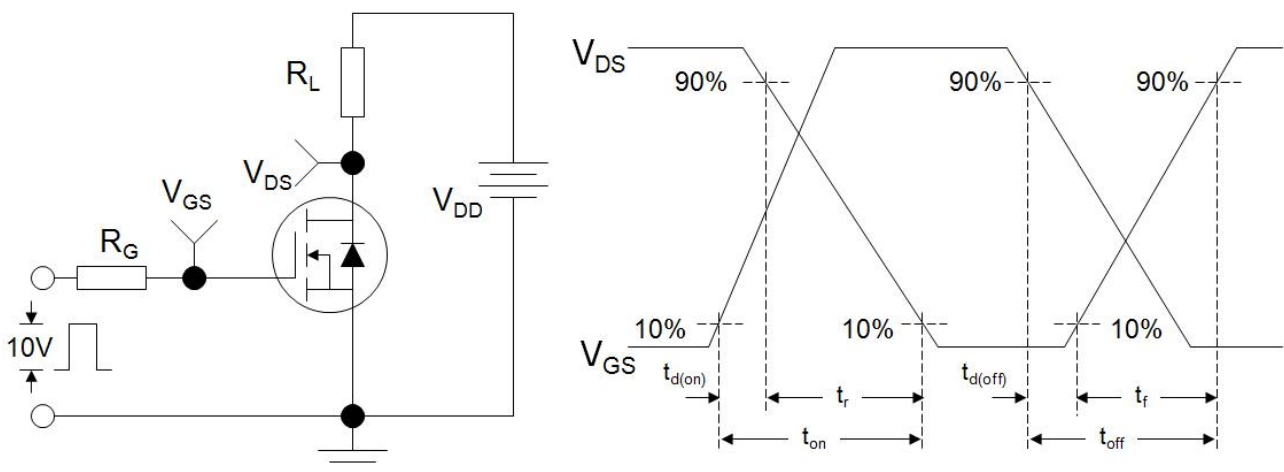
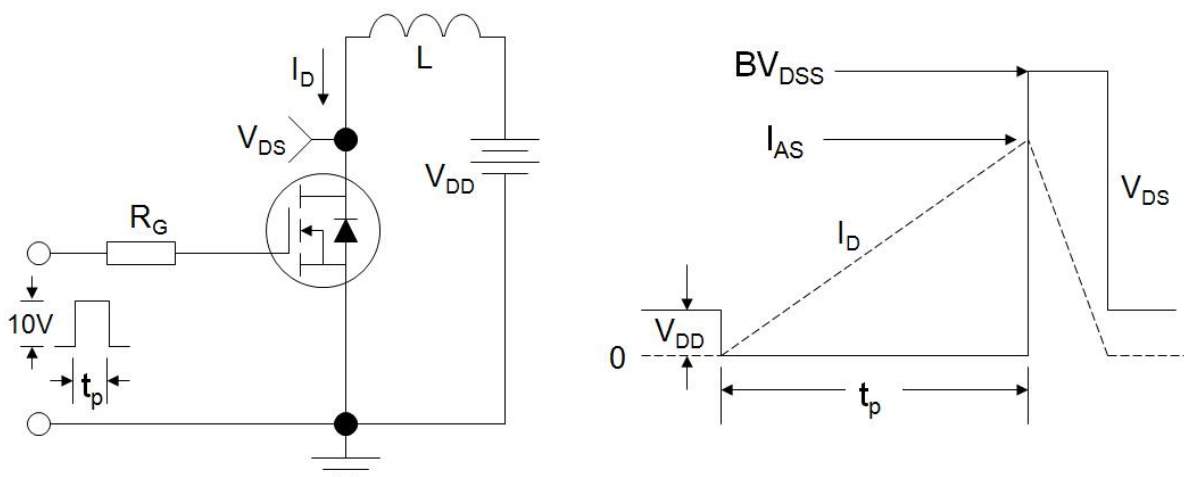
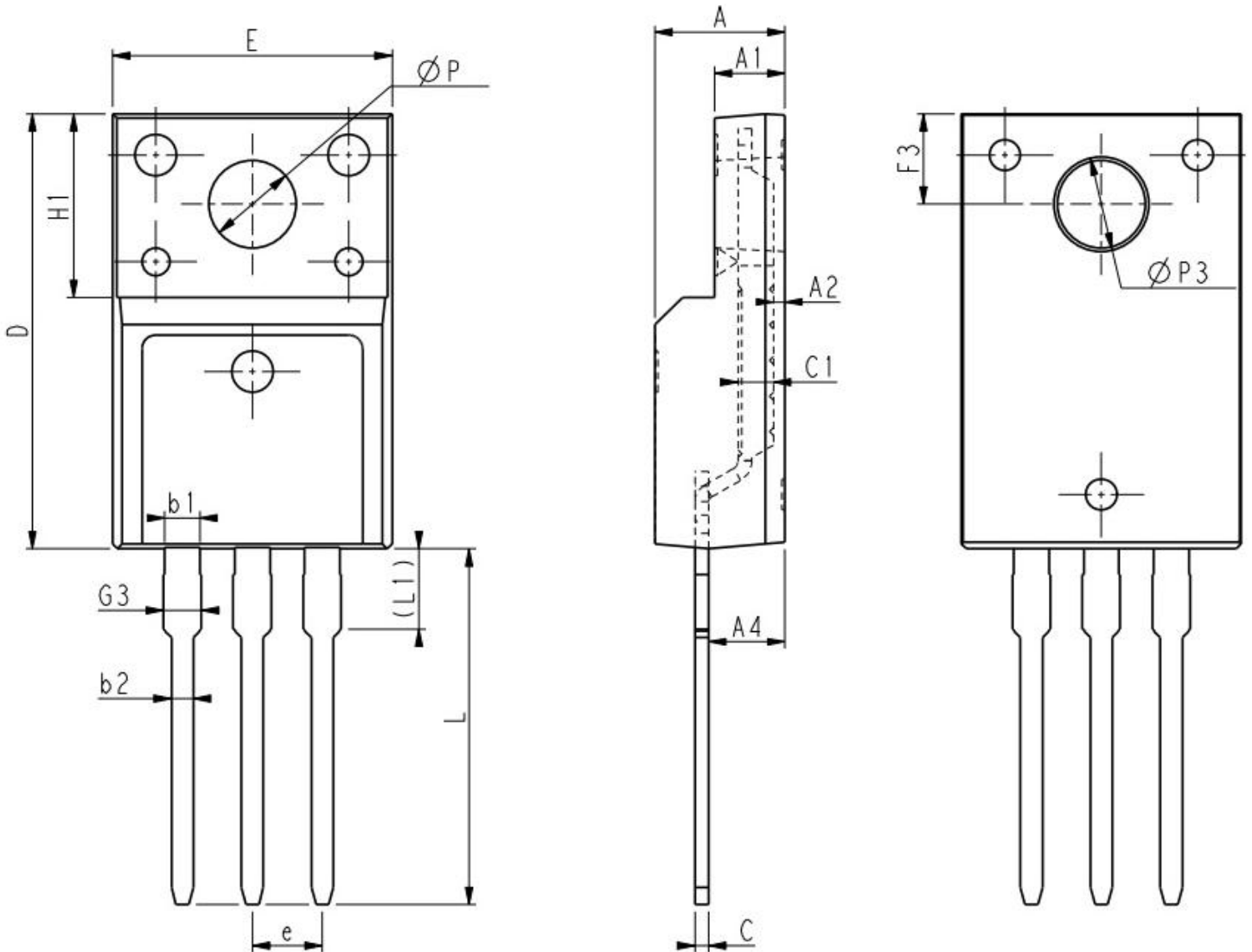


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





TO-220F

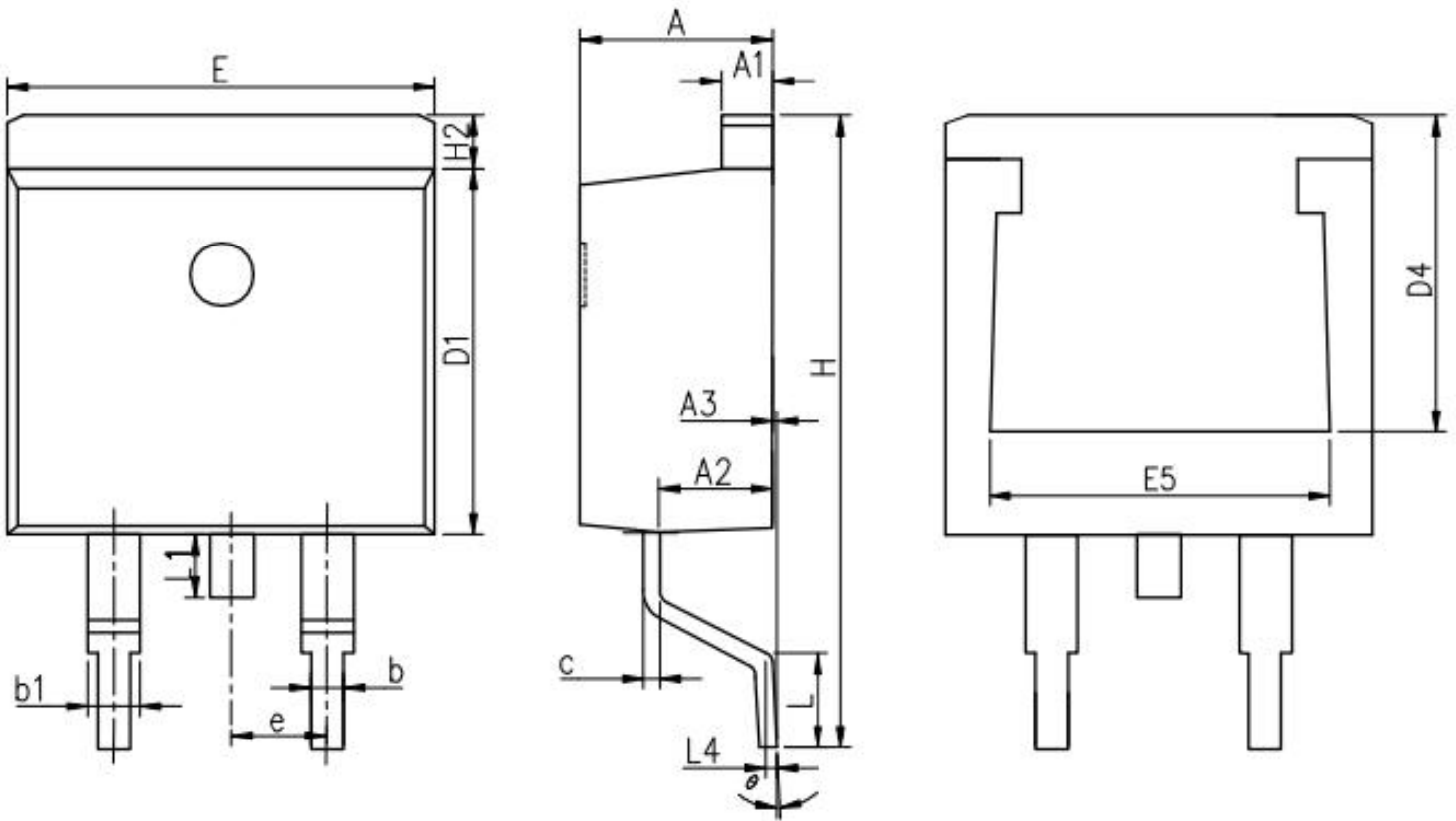


Unit:mm			
Symbol	Min.	Nom	Max.
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.93	3.03	3.13
ΦP	3.03	3.18	3.38
$\Phi P3$	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95



TO-263

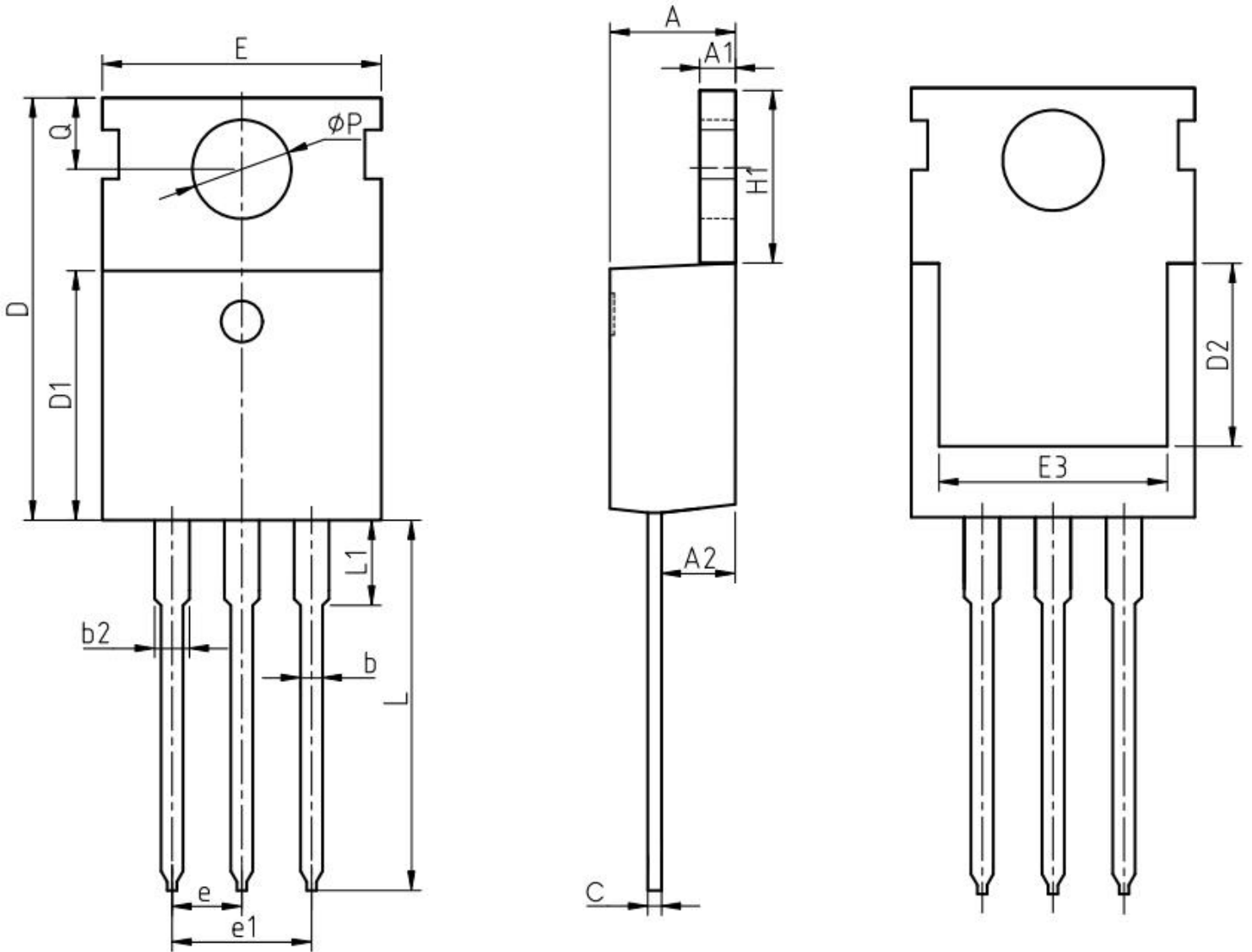


Unit:mm			
Symbol	Min.	Nom	Max.
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
E	9.86	10.16	10.36
E5	7.06	-	-
e	2.54BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.30	2.60
L1	1.40	1.55	1.70
L4	0.25BSC		
theta	0°	5°	9°



TO-220

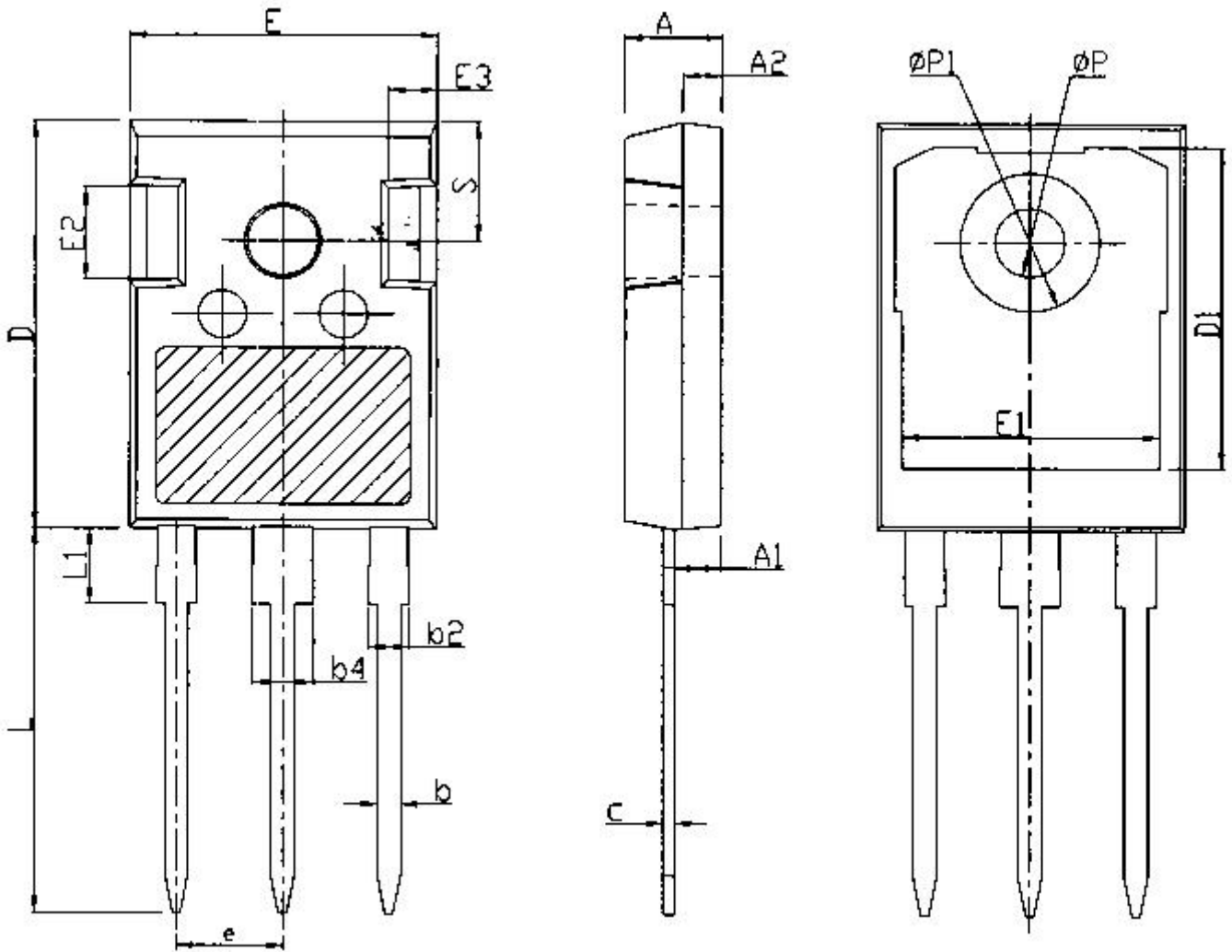


Unit:mm			
Symbol	Min.	Nom	Max.
A	4.37	4.57	4.77
A1	1.25	1.30	1.40
A2	2.20	2.40	2.60
b	0.70	0.80	0.95
b2	1.17	1.27	1.47
c	0.45	0.50	0.60
D	15.10	15.60	16.10
D1	8.80	9.10	9.40
D2	5.50	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
E	9.70	10.00	10.30
E3	7.00	-	-
e	2.54 BSC		
e1	5.08 BSC		
H1	6.25	6.50	6.85
L	12.75	13.50	13.80
L1	-	3.10	3.40
ΦP	3.40	3.60	3.80
Q	2.60	2.80	3.00



TO-247



Unit:mm			
Symbol	Min.	Nom	Max.
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
b4	2.91	3.01	3.21
c	0.51	0.61	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85

Unit:mm			
Symbol	Min.	Nom.	Max.
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	5.44BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
φP	3.40	3.60	3.80
φP1	-	-	7.30
S	6.15BSC		



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